Izabella Grzegory

List of Publications by Year in Descending Order

418 papers	11,308 citations	50 h-index	91 g-index
443 ext. papers	12,036 ext. citations	2.3 avg, IF	5.41 L-index

#	Paper	IF	Citations
418	Recent Progress in Crystal Growth of Bulk GaN. *Acta Physica Polonica A*, **2022**, 141, 167-174	0.6	
417	On Stress-Induced Polarization Effect in Ammonothermally Grown GaN Crystals. *Crystals*, **2022**, 12, 554	2.3	1
416	Nitrogen Dissolution in Liquid Ga and Fe: Comprehensive Analysis, Relevance for Crystallization of GaN. *Materials*, **2021**, 14,	3.5	2
415	Adsorption of nitrogen at AlN(000-1) surface Decisive role of structural and electronic factors. *Surface Science*, **2021**, 713, 121891	1.8	0
414	Complex Geometric Structure of a Simple Solid-Liquid Interface: GaN(0001)-Ga. *Physical Review Letters*, **2020**, 124, 086101	7.4	3
413	Experimental and theoretical evidence of the temperature-induced wurtzite to rocksalt phase transition in GaN under high pressure. *Physical Review B*, **2020**, 102,	3.3	5
412	Catalytic Synthesis of Nitric Monoxide at the AlN(0001) Surface: Ab Initio Analysis. *Journal of Physical Chemistry C*, **2019**, 123, 10893-10906	3.8	3
411	Iron and manganese as dopants used in the crystallization of highly resistive HVPE-GaN on native seeds. *Japanese Journal of Applied Physics*, **2019**, 58, SC1047	1.4	12
410	Homoepitaxial growth by halide vapor phase epitaxy of semi-polar GaN on ammonothermal seeds. *Japanese Journal of Applied Physics*, **2019**, 58, SC1030	1.4	6
409	Physical properties of Ga-Fe-N system relevant for crystallization of GaN Initial studies. *Journal of Crystal Growth*, **2019**, 507, 77-86	1.6	1
408	Melting of tetrahedrally bonded semiconductors: nomaly of the phase diagram of GaN?. *Journal of Crystal Growth*, **2019**, 505, 5-9	1.6	4
407	First Step in Exploration of Fe Ga N System for Efficient Crystallization of GaN at High N2 Pressure. *Physica Status Solidi (A) Applications and Materials Science*, **2018**, 215, 1700897	1.6	2
406	Adsorption of N2 and H2 at AlN(0001) Surface: Ab Initio Assessment of the Initial Stage of Ammonia Catalytic Synthesis. *Journal of Physical Chemistry C*, **2018**, 122, 20301-20311	3.8	8
405	Correlating compositional, structural and optical properties of InGaN quantum wells by transmission electron microscopy **2018**, 267-272		
404	Influence of edge-grown HVPE GaN on the structural quality of c-plane oriented HVPE-GaN grown on ammonothermal GaN substrates. *Journal of Crystal Growth*, **2016**, 456, 80-85	1.6	16
403	High Temperature Stability of Electrical and Optical Properties of Bulk GaN:Mg Grown by HNPS Method in Different Crystallographic Directions. *Acta Physica Polonica A*, **2016**, 129, A-126-A-128	0.6	1
402	Diffusion of oxygen in bulk GaN crystals at high temperature and at high pressure. *Journal of Crystal Growth*, **2016**, 449, 35-42	1.6	6

401	Preparation of a smooth GaN□allium solid□quid interface. *Journal of Crystal Growth*, **2016**, 448, 70-75	1.6	6
400	HVPE-GaN growth on GaN-based Advanced Substrates by Smart Cut□*Journal of Crystal Growth*, **2016**, 456, 73-79	1.6	7
399	Homoepitaxial growth of HVPE-GaN doped with Si. *Journal of Crystal Growth*, **2016**, 456, 91-96	1.6	17
398	Growth of HVPE-GaN on native seeds □umerical simulation based on experimental results. *Journal of Crystal Growth*, **2016**, 456, 86-90	1.6	8
397	Influence of crystallization front direction on the Mg-related impurity centers incorporation in bulk GaN:Mg grown by HNPS method. *Optical Materials*, **2016**, 58, 491-496	3.3	1
396	Homoepitaxial HVPE GaN growth on non- and semi-polar seeds **2015**,		3
395	The challenge of decomposition and melting of gallium nitride under high pressure and high temperature. *Journal of Physics and Chemistry of Solids*, **2015**, 85, 138-143	3.9	29
394	Examination of defects and the seed's critical thickness in HVPE-GaN growth on ammonothermal GaN seed. *Physica Status Solidi (B): Basic Research*, **2015**, 252, 1172-1179	1.3	26
393	HVPE-GaN grown on MOCVD-GaN/sapphire template and ammonothermal GaN seeds: Comparison of structural, optical, and electrical properties. *Journal of Crystal Growth*, **2014**, 394, 55-60	1.6	37
392	True-blue laser diodes grown by plasma-assisted MBE on bulk GaN substrates. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2014**, 11, 666-669		1
391	Examination of growth rate during hydride vapor phase epitaxy of GaN on ammonothermal GaN seeds. *Journal of Crystal Growth*, **2014**, 407, 52-57	1.6	18
390	HVPE-GaN growth on misoriented ammonothermal GaN seeds. *Journal of Crystal Growth*, **2014**, 403, 32-37	1.6	13
389	Structural defects in bulk GaN. *Journal of Crystal Growth*, **2014**, 403, 66-71	1.6	5
388	Homoepitaxial HVPE-GaN growth on non-polar and semi-polar seeds. *Journal of Crystal Growth*, **2014**, 403, 48-54	1.6	28
387	Photo-etching of HVPE-grown GaN: Revealing extended non-homogeneities induced by periodic carrier gas exchange. *Journal of Crystal Growth*, **2014**, 403, 77-82	1.6	5
386	A Monolithic White-Light LED Based on GaN Doped with Be. *Advances in Science and Technology*, **2014**, 93, 264-269	0.1	1
385	Preparation of free-standing GaN substrates from GaN layers crystallized by hydride vapor phase epitaxy on ammonothermal GaN seeds. *Japanese Journal of Applied Physics*, **2014**, 53, 05FA04	1.4	19
384	Role and influence of impurities on GaN crystal grown from liquid solution under high nitrogen pressure in multi-feed-seed configuration **2013**,		5

383	Analysis of self-lift-off process during HVPE growth of GaN on MOCVD-GaN/sapphire substrates with photolitographically patterned Ti mask. *Journal of Crystal Growth*, **2013**, 380, 99-105	1.6	21
382	GaN doped with beryllium: An effective light converter for white light emitting diodes. *Applied Physics Letters*, **2013**, 103, 011107	3.4	20
381	Preparation of Free-Standing GaN Substrates from Thick GaN Layers Crystallized by Hydride Vapor Phase Epitaxy on Ammonothermally Grown GaN Seeds. *Applied Physics Express*, **2013**, 6, 075504	2.4	43
380	Growth mechanisms in semipolar and nonpolar m-plane AlGaN/GaN structures grown by PAMBE under N-rich conditions. *Journal of Crystal Growth*, **2013**, 377, 184-191	1.6	20
379	HVPE-GaN growth on ammonothermal GaN crystals **2013**,		10
378	Influence of substrate planar defects on MOVPE GaN layer growth. *Physica Status Solidi (A) Applications and Materials Science*, **2013**, 210, 503-506	1.6	1
377	Temperature-Dependence of Exciton Radiative Recombination in (Al,Ga)N/GaN Quantum Wells Grown ona-Plane GaN Substrates. *Japanese Journal of Applied Physics*, **2013**, 52, 08JC01	1.4	8
376	The homoepitaxial challenge: GaN crystals grown at high pressure for laser diodes and laser diode arrays **2013**, 18-77		3
375	Characterization of the Nonpolar GaN Substrate Obtained by Multistep Regrowth by Hydride Vapor Phase Epitaxy. *Applied Physics Express*, **2012**, 5, 011001	2.4	6
374	Multi feed seed (MFS) high pressure crystallization of 1" in GaN. *Journal of Crystal Growth*, **2012**, 350, 5-10	1.6	17
373	Growth of GaN:Mg crystals by high nitrogen pressure solution method in multi-feed-seed configuration. *Journal of Crystal Growth*, **2012**, 350, 50-55	1.6	12
372	Imaging extended non-homogeneities in HVPE grown GaN with Kelvin Probe Microscopy and photo-etching. *Journal of Crystal Growth*, **2012**, 353, 68-71	1.6	5
371	Thermal carrier emission and nonradiative recombinations in nonpolar (Al,Ga)N/GaN quantum wells grown on bulk GaN. *Journal of Applied Physics*, **2012**, 111, 033517	2.5	10
370	Unambiguous relationship between photoluminescence energy and its pressure evolution in InGaN/GaN quantum wells. *Physica Status Solidi (B): Basic Research*, **2012**, 249, 476-479	1.3	1
369	High nitrogen pressure solution growth of GaN in multi feed-seed configuration. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 453-456		5
368	Nonlinear emission properties of an optically anisotropic GaN-based microcavity. *Physical Review B*, **2012**, 86,	3.3	5
367	The nature of Cr center in GaN: Magnetic anisotropy of GaN:Cr single crystals. *Journal of Applied Physics*, **2012**, 112, 113914	2.5	4
366	Observation of Magnetic Anisotropy in GaN:Cr Single Crystals. *Acta Physica Polonica A*, **2012**, 122, 1007-1009		10

365	High nitrogen pressure solution (HNPS) growth of GaN on 2 inch free standing GaN substrates. *Science China Technological Sciences*, **2011**, 54, 42-46	3.5	6
364	High nitrogen pressure solution growth of bulk GaN in "seed-seed" configuration. *Physica Status Solidi (A) Applications and Materials Science*, **2011**, 208, 1507-1510	1.6	8
363	C-plane bowing in free standing GaN crystals grown by HVPE on GaN-sapphire substrates with photolithographically patterned Ti masks. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2117-2119		10
362	Growth mechanism of InGaN by plasma assisted molecular beam epitaxy. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2011**, 29, 03C136	1.3	23
361	Electron spin resonance and Rashba field in GaN-based materials. *Physica B: Condensed Matter*, **2011**, 406, 2548-2554	2.8	8
360	Tailoring the light-matter coupling in anisotropic microcavities: Redistribution of oscillator strength in strained m-plane GaN/AlGaN quantum wells. *Physical Review B*, **2011**, 84,	3.3	13
359	Properties of metal-insulator transition and electron spin relaxation in GaN:Si. *Physical Review B*, **2011**, 83,	3.3	26
358	High quality m-plane GaN grown under nitrogen-rich conditions by plasma assisted molecular beam epitaxya). *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2011**, 29, 03C135	1.3	9
357	Intrinsic dynamics of weakly and strongly confined excitons in nonpolar nitride-based heterostructures. *Physical Review B*, **2011**, 83,	3.3	26
356	Mismatch relaxation by stacking fault formation of AlN islands in AlGaN/GaN structures on m-plane GaN substrates. *Applied Physics Letters*, **2011**, 99, 061901	3.4	12
355	Step-flow anisotropy of the m-plane GaN (11$\bar{2}$00) grown under nitrogen-rich conditions by plasma-assisted molecular beam epitaxy. *Physical Review B*, **2011**, 83,	3.3	17
354	Processing of Mechanically Polished Surfaces of Bulk GaN Substrates. *ECS Transactions*, **2011**, 41, 149-156		1
353	InAlGaN laser diodes grown by plasma assisted molecular beam epitaxy. *Lithuanian Journal of Physics*, **2011**, 51, 276-282	1.1	0
352	GaN Bulk Substrates Grown under Pressure from Solution in Gallium **2010**, 173-207		2
351	Hole carrier concentration and photoluminescence in magnesium doped InGaN and GaN grown on sapphire and GaN misoriented substrates. *Journal of Applied Physics*, **2010**, 108, 023516	2.5	14
350	Growth of Bulk GaN Crystals by HVPE on Single Crystalline GaN Seeds. *Springer Series in Materials Science*, **2010**, 61-78	0.9	4
349	Tilt of InGaN layers on miscut GaN substrates. *Physica Status Solidi - Rapid Research Letters*, **2010**, 4, 142-144	1.5	9
348	. *Proceedings of the IEEE*, **2010**, 98, 1214-1219	14.3	15

347	High temperature chemical and physical changes of the HVPE-prepared GaN semiconductor. *Materials Chemistry and Physics*, **2010**, 122, 537-543	4.4	8
346	Ca3N2 as a flux for crystallization of GaN. *Journal of Crystal Growth*, **2010**, 312, 2574-2578	1.6	1
345	The influence of indium on the growth of GaN from solution under high pressure. *Journal of Crystal Growth*, **2010**, 312, 2593-2598	1.6	3
344	Revealing extended defects in HVPE-grown GaN. *Journal of Crystal Growth*, **2010**, 312, 2611-2615	1.6	22
343	High Pressure Solution Growth of Gallium Nitride. *Springer Series in Materials Science*, **2010**, 207-234	0.9	12
342	Application of a composite plasmonic substrate for the suppression of an electromagnetic mode leakage in InGaN laser diodes. *Applied Physics Letters*, **2009**, 95, 261108	3.4	24
341	Different pressure behavior of GaN/AlGaN quantum structures grown along polar and nonpolar crystallographic directions. *Journal of Applied Physics*, **2009**, 105, 063104	2.5	19
340	MAGNETO-LUMINESCENCE OF GADOLINIUM DOPED GALLIUM NITRIDE. *International Journal of Modern Physics B*, **2009**, 23, 2994-2998	1.1	0
339	Nitride-based quantum structures and devices on modified GaN substrates. *Physica Status Solidi (A) Applications and Materials Science*, **2009**, 206, 1130-1134	1.6	15
338	Bulk GaN crystals and wafers grown by HVPE without intentional doping. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, S297-S300		10
337	What is new in nitride laser diodes reliability studies. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, S881-S884		
336	InGaN light emitting diodes for 415 nm–420 nm spectral range by plasma assisted MBE. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, S917-S920		29
335	Carrier recombination under one-photon and two-photon excitation in GaN epilayers. *Micron*, **2009**, 40, 118-21	2.3	2
334	Structural defects in GaN crystals grown by HVPE on needle-shaped GaN seeds obtained under high N2 pressure. *Journal of Crystal Growth*, **2009**, 311, 1407-1410	1.6	1
333	Nitride-based laser diodes by plasma-assisted MBE–from violet to green emission. *Journal of Crystal Growth*, **2009**, 311, 1632-1639	1.6	43
332	Why InGaN laser-diode degradation is accompanied by the improvement of its thermal stability **2008**,		7
331	Nonradiative recombination at threading dislocations in n-type GaN: Studied by cathodoluminescence and defect selective etching. *Applied Physics Letters*, **2008**, 92, 231909	3.4	63
330	Substrate misorientation induced strong increase in the hole concentration in Mg doped GaN grown by metalorganic vapor phase epitaxy. *Applied Physics Letters*, **2008**, 93, 172117	3.4	26

329	Influence of substrate misorientation on properties of InGaN layers grown on freestanding GaN. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 1485-1487		11
328	Liquid phase epitaxy of GaN on MOCVD GaN/sapphire and HVPE free-standing substrates under high nitrogen pressure. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 1539-1542		1
327	Optically pumped lasing of GaN/AlGaN structures grown along a non-polar crystallographic direction. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 2173-2175		
326	High rate photoelectrochemical etching of GaN and the use of patterned substrates for HVPE regrowth. *Journal of Crystal Growth*, **2008**, 310, 3478-3481	1.6	3
325	Fabrication and properties of GaN-based lasers. *Journal of Crystal Growth*, **2008**, 310, 3979-3982	1.6	10
324	Growth of InGaN and InGaN/InGaN quantum wells by plasma-assisted molecular beam epitaxy. *Journal of Crystal Growth*, **2008**, 310, 3983-3986	1.6	32
323	GaN crystallization by the high-pressure solution growth method on HVPE bulk seed. *Journal of Crystal Growth*, **2008**, 310, 3924-3933	1.6	31
322	Time-Resolved Studies of Gallium Nitride Doped with Gadolinium. *Acta Physica Polonica A*, **2008**, 114, 1425-1430	0.6	2
321	LASER DIODES GROWN ON BULK GALLIUM NITRIDE SUBSTRATES **2008**, 223-252		
320	Modelling the growth of nitrides in ammonia-rich environment. *Crystal Research and Technology*, **2007**, 42, 1281-1290	1.3	10
319	Magneto-optical studies of iron impurity in HVPE GaN. *Physica B: Condensed Matter*, **2007**, 401-402, 458-461	1.1	3
318	Crystallization of low dislocation density GaN by high-pressure solution and HVPE methods. *Journal of Crystal Growth*, **2007**, 300, 17-25	1.6	26
317	Adsorption and dissolution of nitrogen in lithium QM DFT investigation. *Journal of Crystal Growth*, **2007**, 304, 299-309	1.6	
316	Platelets and needles: Two habits of pressure-grown GaN crystals. *Journal of Crystal Growth*, **2007**, 305, 414-420	1.6	7
315	Orthodox etching of HVPE-grown GaN. *Journal of Crystal Growth*, **2007**, 305, 384-392	1.6	102
314	Role of dislocation-free GaN substrates in the growth of indium containing optoelectronic structures by plasma-assisted MBE. *Journal of Crystal Growth*, **2007**, 305, 346-354	1.6	18
313	High pressure high temperature seeded growth of GaN on 1 in sapphire/GaN templates: Analysis of convective transport. *Journal of Crystal Growth*, **2007**, 307, 259-267	1.6	16
312	Optical gain and saturation behavior in homoepitaxially grown InGaN/GaN/AlGaN laser structures. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2007**, 4, 82-85		

311	Platelets and needles: two habits of pressure grown GaN crystals. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2007**, 4, 2236-2239		1
310	Capture kinetics at deep-level electron traps in GaN-based laser diode. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2007**, 4, 2878-2882		6
309	Gain mechanisms in field-free InGaN layers grown on sapphire and bulk GaN substrate. *Physica Status Solidi - Rapid Research Letters*, **2007**, 1, 141-143	2.5	3
308	Comparison of gain in group-III-nitride laser structures grown by metalorganic vapour phase epitaxy and plasma-assisted molecular beam epitaxy on bulk GaN substrates. *Semiconductor Science and Technology*, **2007**, 22, 736-741	1.8	3
307	Optically pumped GaN□AlGaN separate-confinement heterostructure laser grown along the (112□0) nonpolar direction. *Applied Physics Letters*, **2007**, 90, 081104	3.4	14
306	Strain-compensated AlGaN□GaN□InGaN cladding layers in homoepitaxial nitride devices. *Applied Physics Letters*, **2007**, 91, 231914	3.4	13
305	Correlation between luminescence and compositional striations in InGaN layers grown on miscut GaN substrates. *Applied Physics Letters*, **2007**, 91, 211904	3.4	35
304	Mode dynamics of high power (InAl)GaN based laser diodes grown on bulk GaN substrate. *Journal of Applied Physics*, **2007**, 101, 083109	2.5	12
303	Tunable broad-area InGaN laser diodes in external cavity **2007**,		2
302	Deep-Level Defects in MBE-Grown GaN-Based Laser Structure. *Acta Physica Polonica A*, **2007**, 112, 331-336	0.6	2
301	Optically Pumped Laser Action on Nitride Based Separate Confinement Heterostructures Grown along the (11□20) Crystallographic Direction. *Acta Physica Polonica A*, **2007**, 112, 467-472	0.6	
300	Magnetoluminescence Studies of GaN:Fe. *Acta Physica Polonica A*, **2007**, 112, 177-182	0.6	
299	Growth of thin AlInN□GaInN quantum wells for applications to high-speed intersubband devices at telecommunication wavelengths. *Journal of Vacuum Science & Technology B*, **2006**, 24, 1505		24
298	Carrier recombination and diffusion in GaN revealed by transient luminescence under one-photon and two-photon excitations. *Applied Physics Letters*, **2006**, 89, 172119	3.4	17
297	60mW continuous-wave operation of InGaN laser diodes made by plasma-assisted molecular-beam epitaxy. *Applied Physics Letters*, **2006**, 88, 221108	3.4	45
296	Degradation mechanisms in InGaN laser diodes grown on bulk GaN crystals. *Applied Physics Letters*, **2006**, 88, 201111	3.4	64
295	Effect of high-temperature annealing on the residual strain and bending of freestanding GaN films grown by hydride vapor phase epitaxy. *Applied Physics Letters*, **2006**, 88, 141909	3.4	27
294	Anomalous temperature characteristics of single wide quantum well InGaN laser diode. *Applied Physics Letters*, **2006**, 88, 071121	3.4	19

293	Negative differential resistance in dislocation-free GaN/AlGaN double-barrier diodes grown on bulk GaN. *Applied Physics Letters*, **2006**, 88, 172106	3.4	90
292	GaN surface doped with Fe atoms. *Journal of Alloys and Compounds*, **2006**, 423, 136-138	5.7	3
291	Growth and characterization of AlInN/GaInN quantum wells for high-speed intersubband devices at telecommunication wavelengths **2006**,		3
290	Growth of bulk GaN by HVPE on pressure grown seeds **2006**,		12
289	Growth of GaN on patterned GaN/sapphire substrates with various metallic masks by high pressure solution method **2006**,		2
288	Broad-area high-power CW operated InGaN laser diodes **2006**, 6133, 168		5
287	High-Pressure Crystallization of GaN **2006**, 1-43		
286	Crystallization of free standing bulk GaN by HVPE. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 1453-1456		8
285	Growth of GaN on patterned thick HVPE free standing GaN substrates by high pressure solution method. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 1487-1490		1
284	Barrier-to-well carrier dynamics of InGaN/GaN multi-quantum-wells grown by plasma assisted MBE on bulk GaN substrates. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 1962-1965		1
283	Screening of polarization induced electric fields in blue/violet InGaN/GaN laser diodes by Si doping in quantum barriers revealed by hydrostatic pressure. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 2303-2306		3
282	Optical properties of InGaN/GaN quantum wells on sapphire and bulk GaN substrate. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 2078-2081		1
281	Mass flow and reaction analysis of the growth of GaN by HVPE. *Physica Status Solidi (A) Applications and Materials Science*, **2006**, 203, 131-134	1.6	2
280	Crystallization of GaN by HVPE on pressure grown seeds. *Physica Status Solidi (A) Applications and Materials Science*, **2006**, 203, 1654-1657	1.6	6
279	Towards identification of degradation mechanisms in InGaN laser diodes grown on bulk GaN crystals. *Physica Status Solidi (A) Applications and Materials Science*, **2006**, 203, 1778-1782	1.6	4
278	Role of band potential roughness on the luminescence properties of InGaN quantum wells grown by MBE on bulk GaN substrates. *Physica Status Solidi (B): Basic Research*, **2006**, 243, 1614-1618	1.3	6
277	Etching, Raman and PL study of thick HVPE-grown GaN. *Materials Science in Semiconductor Processing*, **2006**, 9, 175-179	4.3	14
276	Selective etching of dislocations in violet-laser diode structures. *Journal of Crystal Growth*, **2006**, 293, 18-21	1.6	15

275	CFD and reaction computational analysis of the growth of GaN by HVPE method. *Journal of Crystal Growth*, **2006**, 296, 31-42	1.6	19
274	Atomically flat GaMnN by diffusion of Mn into GaN(0001). *Superlattices and Microstructures*, **2006**, 40, 607-611	2.8	7
273	Resonant photoemission study of Ti interaction with GaN surface. *Surface Science*, **2006**, 600, 873-879	1.8	2
272	Crack Free GaInN/AlInN Multiple Quantum Wells Grown on GaN with Strong Intersubband Absorption at 1.55 m. *Acta Physica Polonica A*, **2006**, 110, 175-181	0.6	3
271	Photoluminescence and Electron Paramagnetic Resonance Studies of Bulk GaN Doped with Gadolinium. *Acta Physica Polonica A*, **2006**, 110, 243-248	0.6	14
270	High Power Continuous Wave Blue InAlGaN Laser Diodes Made by Plasma Assisted MBE. *Acta Physica Polonica A*, **2006**, 110, 345-351	0.6	1
269	The influence of lattice parameter variation on microstructure of GaN single crystals. *Journal of Alloys and Compounds*, **2005**, 401, 261-264	5.7	34
268	High power blue violet InGaN laser diodes grown on bulk GaN substrates by plasma-assisted molecular beam epitaxy. *Semiconductor Science and Technology*, **2005**, 20, 809-813	1.8	30
267	Fully-screened polarization-induced electric fields in blue violet InGaN GaN light-emitting devices grown on bulk GaN. *Applied Physics Letters*, **2005**, 87, 041109	3.4	37
266	Properties of violet laser diodes grown on bulk GaN substrates **2005**,		4
265	Growth of AlN, GaN and InN from the solution. *International Journal of Materials and Product Technology*, **2005**, 22, 226	1	19
264	Gallium nitride growth on sapphire/GaN templates at high pressure and high temperatures. *Journal of Crystal Growth*, **2005**, 274, 55-64	1.6	18
263	Growth of GaN on patterned GaN/sapphire substrates by high pressure solution method. *Journal of Crystal Growth*, **2005**, 281, 11-16	1.6	7
262	Properties of InGaN blue laser diodes grown on bulk GaN substrates. *Journal of Crystal Growth*, **2005**, 281, 107-114	1.6	6
261	Defects in GaN single crystals and homoepitaxial structures. *Journal of Crystal Growth*, **2005**, 281, 135-142	1.6	22
260	Influence of dislocation and ionized impurity scattering on the electron mobility in GaN/AlGaN heterostructures. *Journal of Crystal Growth*, **2005**, 281, 194-201	1.6	6
259	Deposition of thick GaN layers by HVPE on the pressure grown GaN substrates. *Journal of Crystal Growth*, **2005**, 281, 38-46	1.6	63
258	Selective etching and TEM study of inversion domains in Mg-doped GaN epitaxial layers. *Journal of Crystal Growth*, **2005**, 282, 45-48	1.6	13

257	Surface and electronic structure of Ga0.92In0.08N thin film investigated by photoelectron spectroscopy. *Thin Solid Films*, **2005**, 476, 396-404	2.2	1
256	Resonant shake-up satellites in photoemission at the Ga 3p photothreshold in GaN. *Solid State Communications*, **2005**, 136, 191-195	1.6	4
255	Bowing of epitaxial layers grown on bulk GaN substrates. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 1259-1264		1
254	Microstructure of III-N semiconductors related to their applications in optoelectronics. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 1366-1373		1
253	Anomalous behaviour of the photoluminescence from GaN/AlGaN quantum wells. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 1010-1013		1
252	Screening of built-in electric fields in group III-nitride laser diodes observed by means of hydrostatic pressure. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 1019-1022		1
251	Bowing of GaN bulk crystals with mismatched epitaxial structures of (AlInGa)N. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 1031-1034		2
250	Localization Effects in InGaN/GaN Double Heterostructure Laser Diode Structures Grown on Bulk GaN Crystals. *Japanese Journal of Applied Physics*, **2005**, 44, 7244-7249	1.4	2
249	Microstructure of InGaN quantum wells grown on GaN single crystals and sapphire. *Journal Physics D: Applied Physics*, **2005**, 38, A89-A92	3	1
248	Efficient radiative recombination and potential profile fluctuations in low-dislocation InGaN□GaN multiple quantum wells on bulk GaN substrates. *Journal of Applied Physics*, **2005**, 97, 103507	2.5	20
247	Blue-violet InGaN laser diodes grown on bulk GaN substrates by plasma-assisted molecular-beam epitaxy. *Applied Physics Letters*, **2005**, 86, 011114	3.4	62
246	Magnetic anisotropy of bulk GaN:Mn single crystals codoped with Mg acceptors. *Physical Review B*, **2005**, 71,	3.3	30
245	Free and bound excitons in GaN□AlGaN homoepitaxial quantum wells grown on bulk GaN substrate along the nonpolar (112□0) direction. *Applied Physics Letters*, **2005**, 86, 162112	3.4	25
244	Effect of growth polarity on vacancy defect and impurity incorporation in dislocation-free GaN. *Applied Physics Letters*, **2005**, 86, 031915	3.4	80
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